







IFN113 N-Channel JFET

Features

• InterFET N0132S Geometry

Low Noise: 1.2 nV/VHz TypicalHigh Gain: 15mS Typical

· RoHS Compliant

• SMT, TH, and Bare Die Package options.

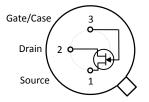
Applications

- · Low-Noise, High Gain
- · Replacement for Japanese 2SK113

Description

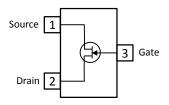
The -50V InterFET IFN113 is a low noise high gain replacement for the Japanese 2SK113 JFET. Gate leakages are typically less than 50pA at room temperatures. The TO-18 package is hermetically sealed and suitable for military applications.

TO-18 Bottom View



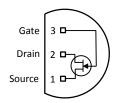


SOT23 Top View





TO-92 Bottom View





Product Summary

	Parameters	IFN113 Min	Unit		
BV _{GSS}	Gate to Source Breakdown Voltage	-50	V		
I _{DSS}	Drain to Source Saturation Current	5	mA		
V _{GS(off)}	Gate to Source Cutoff Voltage	-0.3	V		
GFS	Forward Transconductance	5	mS		

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
IFN113	Through-Hole	TO-18	Bulk
PN113	Through-Hole	TO-92	Bulk
SMP113	Surface Mount	SOT23	Bulk
	7" Tape and Reel: Max 3,000 Pieces		Minimum 1,000 Pieces
SMP113TR	13" Tape and Reel: Max 9,000 Pieces	SOT23	Tape and Reel
IFN113COT	Chip Orientated Tray (COT Waffle Pack)	СОТ	400/Waffle Pack
IFN113CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.









Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

	Parameters	Value	Unit
V_{RGS}	Reverse Gate Source and Gate Drain Voltage	-50	V
I _{FG}	Continuous Forward Gate Current	10	mA
PD	Continuous Device Power Dissipation	360	mW
Р	Power Derating	2.88	mW/°C
Tı	Operating Junction Temperature	-55 to 125	°C
T _{STG}	Storage Temperature	-65 to 200	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

			IFN113		
	Parameters	Conditions	Min	Max	Unit
V _{(BR)GSS}	Gate to Source Breakdown Voltage	V _{DS} = 0V, I _G = -1μA	-50		V
I _{GSS}	Gate to Source Reverse Current	V _{GS} = -20V, V _{DS} = 0V		-1	nA
V _{GS(OFF)}	Gate to Source Cutoff Voltage	V _{DS} = 20V, I _D = 100nA	-0.3	-10	V
I _{DSS}	Drain to Source Saturation Current	$V_{GS} = 0V$, $V_{DS} = 20V$ (Pulsed)	5	150	mA

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

			IFN113		
	Parameters	Conditions	Min	Max	Unit
GFS	Forward Transconductance	V _{DS} = 20V, V _{GS} = 0V, f = 1kHz	5	50	mS
Ciss	Input Capacitance	V _{DS} = 20V, V _{GS} = 0V, f = 1MHz	12 (typ)		pF
Crss	Reverse Transfer Capacitance	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz	3 (typ)		рF
e _n	Equivalent Circuit Input Noise Voltage	V _{DS} = 10V, I _D = 5mA, f = 1kHz	1.2 (typ)		nV/√Hz



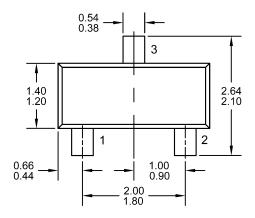


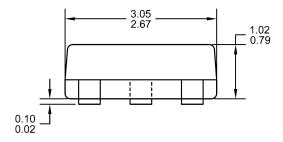


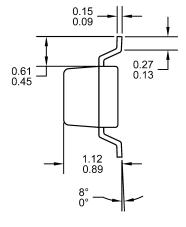


SOT23 (TO-236AB) Mechanical and Layout Data

Package Outline Data

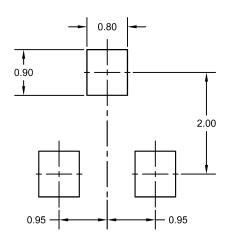






- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.12 grams
- 3. Molded plastic case UL 94V-0 rated
- For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
- Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

Suggested Pad Layout



- L. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.



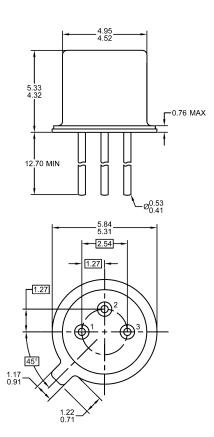






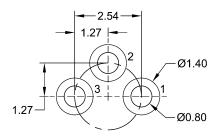
TO-18 Mechanical and Layout Data

Package Outline Data



- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.29 grams
- 3. Bulk product is shipped in standard ESD shipping material
- 4. Refer to JEDEC standards for additional information.

Suggested Through-Hole Layout



- 1. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.



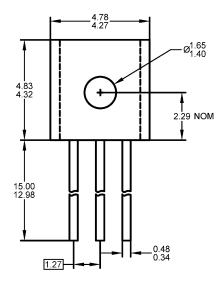


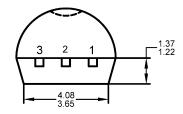


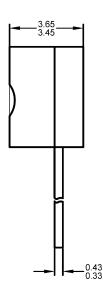


TO-92 Mechanical and Layout Data

Package Outline Data

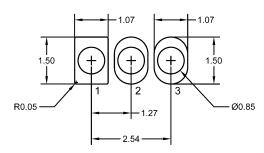






- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.19 grams
- 3. Molded plastic case UL 94V-0 rated
- Bulk product is shipped in standard ESD shipping material
- 5. Refer to JEDEC standards for additional information.

Suggested Through-Hole Layout



- 1. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.